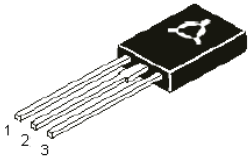
Medium Power PNP Transistor

multicomp PRO



Pin Configuration:
1. Emitter
2. Collector
3. Base

Feature:

- PNP Plastic Medium Power Silicon Transistor
- Designed for use Line-Operated Applications Such as Low Power, Line Operated Series Pass and Switching Regulator Requiring PNP Capability

Absolute Maximum Ratings

Description	Symbol	Rating	Unit
Collector Base Voltage	V_{CBO}	300	V
Collector Emitter Voltage	V_{CEO}		
Emitter Base Voltage	V_{EBO}	3	
Collector Current Continuous	I_C	500	mA
Power Dissipation at T_c = 25°C Derate above 25°C	P_D	20 0.16	W mW/°C
Operating and Storage Junction Temperature Range	T_j, T_{stg}	-65 to +150	°C

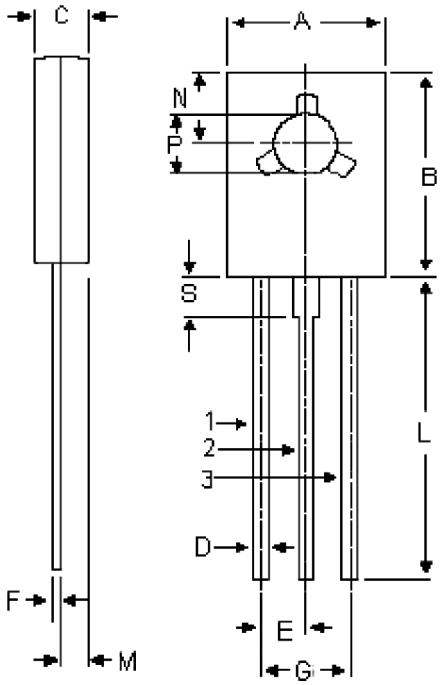
Thermal Resistance

Junction to Case	$R_{th\ (j-c)}$	6.25	°C/W
Junction to Ambient	$R_{th\ (j-a)}$	83.3	

Electrical Characteristics (T_c = 25°C unless specified otherwise)

Parameter	Symbol	Test Condition	Minimum	Maximum	Unit
Collector Emitter Breakdown Voltage	$V_{CEO\ (SUS)}$	I_C = 1mA, I_B = 0	300	-	V
Collector Cut off Current	I_{CBO}	V_{CB} = 300V, I_E = 0	-	100	µA
Emitter Cut off Current	I_{EBO}	V_{EB} = 3V, I_C = 0	-		
DC Current Gain	h_{FE}	I_C = 0.05A, V_{CE} = 10V	30	240	-

Medium Power PNP Transistor



Dimensions	Min.	Max.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 (Typical)	
F	0.49	0.75
G	4.5 (Typical)	
L	15.7 (Typical)	
M	1.27 (Typical)	
N	3.75 (Typical)	
P	3	3.2
S	2.5 (Typical)	

Dimensions : Millimetres

Pin Configuration:

1. Emitter
2. Collector
3. Base

Part Number Table

Description	Part Number
Transistor, PNP, TO-126	MJE350